



Temperature-programmed desorption study of NO reactions on rutile TiO₂(110)-1 × 1



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ABSTRACT

Systematic temperature-programmed desorption (TPD) studies of NO adsorption and reactions on rutile TiO₂(110)-1 × 1 surface reveal several distinct reaction channels in a temperature range of 50–500 K. NO readily reacts on TiO₂(110) to form N₂O, which desorbs between 50 and 200 K (LT N₂O channels), which leaves the TiO₂ surface populated with adsorbed oxygen atoms (O_a) as a by-product of N₂O formation. In addition, we observe simultaneous desorption peaks of NO and N₂O at 270 K (HT1 N₂O) and 400 K (HT2 N₂O), respectively, both of which are attributed to reaction-limited processes. No N-derived reaction product desorbs from TiO₂(110) surface above 500 K or higher, while the surface may be populated with O_a's and oxidized products such as NO₂ and NO₃. The adsorbate-free TiO₂ surface with oxygen vacancies can be regenerated by prolonged annealing at 850 K or higher. Detailed analysis of the three N₂O desorption yields reveals that the surface species for the HT channels are likely to be various forms of NO dimers.

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1. Introduction

As a part of the effort to reduce the NO_x emissions in combustion engines and power plants, a great deal of research has been invested in the design of efficient catalysts for the conversion of NO_x into nontoxic N₂ [1, 2]. In this study, we aim to provide a fundamental level understanding of the underlying mechanism of catalytic reduction of NO [3–5] over TiO₂ catalysts. Such studies should provide a foundation for our understanding of the NO reduction over the TiO₂-based de-NO_x catalysts such as V₂O₅/TiO₂ [6,7], WO₃/TiO₂ [8], V₂O₅-WO₃/TiO₂ [9,10], and V₂O₅-MoO₃/TiO₂ [11].

A great deal of insight has been obtained from studies performed on model rutile TiO₂(110) surfaces [12–16]. It has been shown that NO adsorbs molecularly below ~100 K and desorbs at 120 K [17]. Theoretical calculations revealed that NO binds to titanium sites with N atom with a binding energy of 8.4 kcal/mol [12]. A stronger binding energy of 35 kcal/mol on oxygen vacancy sites has been also predicted by theory. Further, other bonding configurations such as (NO)₂ dimers have been theoretically [12,15] predicted and recently observed experimentally [15,16].

In addition to molecular adsorption, the reactions of NO molecules adsorbed on TiO₂(110) lead to the formation of N₂O, which desorbs in multiple peaks having temperatures of 170, 270, and 400 K [12,14,17].

Irradiation with photons can facilitate the reduction of molecularly adsorbed NO at low temperatures to initiate facile desorption of N₂O [13]. The oxygen atoms left behind, fill bridging oxygen vacancy (V_O's) defect sites effectively oxidizing the surface at the early stage of reaction [17]. According to our recent study [14], the surface charge associated with the V_O's strongly enhances the conversion of NO to N₂O at substrate temperatures as low as 50 K. A fraction of N₂O molecules desorb rapidly at 50 K while the rest can be liberated upon heating to ~180 K.

Although N₂O formation from NO has been observed on TiO₂(110) in previous studies [12–14], the reaction mechanism appears complex and is far from being well-understood. This is clearly illustrated by complex N₂O desorption which exhibits several desorption channels peaking at 170, 270, and 400 K. Further, while the studies [17] performed on reduced TiO₂(110) have shown that surface defects such as V_O's play an important role in NO reduction, the N₂O formation has been also observed on a fully oxidized [12] TiO₂(110) with two desorption peaks at 170 and 250 K.

In this study, we focus on the coverage-dependent reactions of NO on pristine (*p*-TiO₂), reduced (*r*-TiO₂), hydroxylated (*h*-TiO₂), and oxidized TiO₂ (*o*-TiO₂). Our quantitative analysis of the N₂O desorption yields shows interesting details about the nature of the surface species responsible for the HT N₂O desorption channels.

2. Experimental details

The measurements were performed in an ultrahigh vacuum (UHV) molecular beam surface scattering apparatus with a base pressure of

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1×10^{-10} torr equipped with quadrupole mass spectrometer (UTI-100C) that was described previously [18].

The rutile $\text{TiO}_2(110)$ substrate ($10 \times 10 \times 1 \text{ mm}^3$, Princeton Scientific) was mounted on a Ta plate using a ceramic glue and a front retaining ring and its temperature was controlled between 50 and 1000 K [14]. The sample was cleaned by repeated Ne^+ -ion sputtering and annealing to 870 K to prepare a well-ordered rutile $\text{TiO}_2(110)-1 \times 1$ surface as determined from a sharp 1×1 pattern in low-energy electron diffraction (LEED). The concentration of bridging oxygen vacancies (V_{O} 's) was monitored by measuring the area of the recombinative H_2O desorption peak at 500 K in temperature-programmed desorption (TPD) spectra [19–21]. At the early stages of this study (a small number of sputter-anneal cycles), the $\text{TiO}_2(110)$ crystal was transparent, exhibited a sharp 1×1 pattern in LEED, and the V_{O} concentration was negligible based on H_2O TPD. We refer to this *pristine* sample as *p-TiO₂*. With an increasing number (>10) of sputter-anneal cycles, the $\text{TiO}_2(110)$ crystal turned dark blue, and the V_{O} concentration increased to $\sim 5\%$ ($\sim 2.6 \times 10^{13} \text{ cm}^{-2}$) (this sample is referred to as *r-TiO₂*). We have also prepared hydroxylated [22–24] and oxidized [25,26] $\text{TiO}_2(110)$ (referred to as *h-TiO₂* and *o-TiO₂*, respectively). On *h-TiO₂*, the V_{O} defect sites have been reacted away by dosing 2 monolayers (ML) of H_2O on *r-TiO₂* at 50 K followed by annealing to 400 K [19,25]. *o-TiO₂* was prepared by oxidizing *r-TiO₂* with molecular O_2 either by dosing $\sim 2 \times 10^{15} \text{ O}_2/\text{cm}^2$ at 300 K or by an O_2 dose of $1\text{--}5 \times 10^{14} \text{ O}_2/\text{cm}^2$ at 50 K followed by annealing to 300 K [25,26].

Molecular NO was dosed using a neat NO beam (Matheson, CP Grade) at substrate temperatures between 50 and 100 K while recording mass fragments of possible reaction products such as N_2 , N_2O , NO, and NO_2 using a quadrupole mass spectrometer (UTI 100C). The TPD spectra of NO and N_2 were determined by subtracting the contribution of the fragments of N_2O ($m/z = 44$ amu) from $m/z = 30$ (0.38 amu) and $m/z = 28$ (0.15 amu), respectively. The absolute N_2O coverage (in $\text{N}_2\text{O}/\text{cm}^2$) was obtained by comparing the integrated TPD area of the N_2O produced with the TPD spectra from a known amount of N_2O preadsorbed on TiO_2 [27]. The absolute NO dose (in NO/cm^2) was estimated from the plot of integrated area of NO TPD spectra obtained from multilayers of NO dosed on oxidized TiO_2 against the calibrated dose of NO by assuming that the sticking coefficient is unity at the dose temperature.

X-ray photoelectron spectroscopy (XPS) measurements were performed using a hemispherical analyzer (Omicron SPHERA 2000) and x-ray ($\text{Mg K}\alpha$) to confirm that no N species remained on the TiO_2 surface after a few cycles of TPD within detection limit of XPS.

3. Results and Discussion

Fig. 1 shows the TPD spectra of NO, N_2O , and N_2 desorbing after the NO adsorption on *p-TiO₂* and *r-TiO₂*. We find that more NO (N_2O) desorbs from *p-TiO₂* (*r-TiO₂*); that is, more N_2O is formed from NO on *r-TiO₂*, most likely due to the presence of V_{O} 's [14]. Unreacted NO desorbs from both surfaces with TPD peaks at ~ 120 and 270 K and measurable desorption signal extending all the way to 400 K. N_2O , as a major reaction product, desorbs at a number of distinct desorption temperatures. The N_2O desorption at < 200 K is assigned to low-temperature (LT) N_2O . As shown in our previous study, N_2O forms readily even at temperatures as low as 50 K, and its formation is facilitated by the subsurface charge associated with V_{O} 's [14]. On *r-TiO₂*, N_2O formed at the dose temperature may desorb from the surface or may remain physisorbed on the surface and contribute to the observed desorption peaks below 200 K [14].

In addition to the LT N_2O reaction channel, we also observe distinct N_2O desorption peaks at 270 and 400 K, labeled as high-temperature (HT) N_2O (HT N_2O). These HT N_2O TPD peaks are also accompanied by NO desorption. Since these desorption temperatures are much higher than the desorption temperatures of physisorbed NO and N_2O , the HT desorption peaks must result from reaction-limited desorption processes.

Fig. 1 also shows a clearly resolved desorption of N_2 at 250 K [14] in addition to N_2O desorption. The N_2 yield increases proportionally with NO dose up to ~ 1 ML whereupon it saturates at $0.7 \times 10^{13} \text{ N}_2/\text{cm}^2$, corresponding to 3% of the NO dosed. The detailed mechanism of N_2 formation is not understood at this point, but the fact that the N_2 desorption temperature coincides with HT1 N_2O desorption suggests that the same surface species for HT1 N_2O formation is responsible for the reaction-limited N_2 formation.

NO TPD spectra following NO adsorption on *p*- and *r*- TiO_2 as a function of NO dose are shown in Fig. 2. The integrated amounts of desorbing NO are further plotted as a function of NO dose in the inset. At small NO

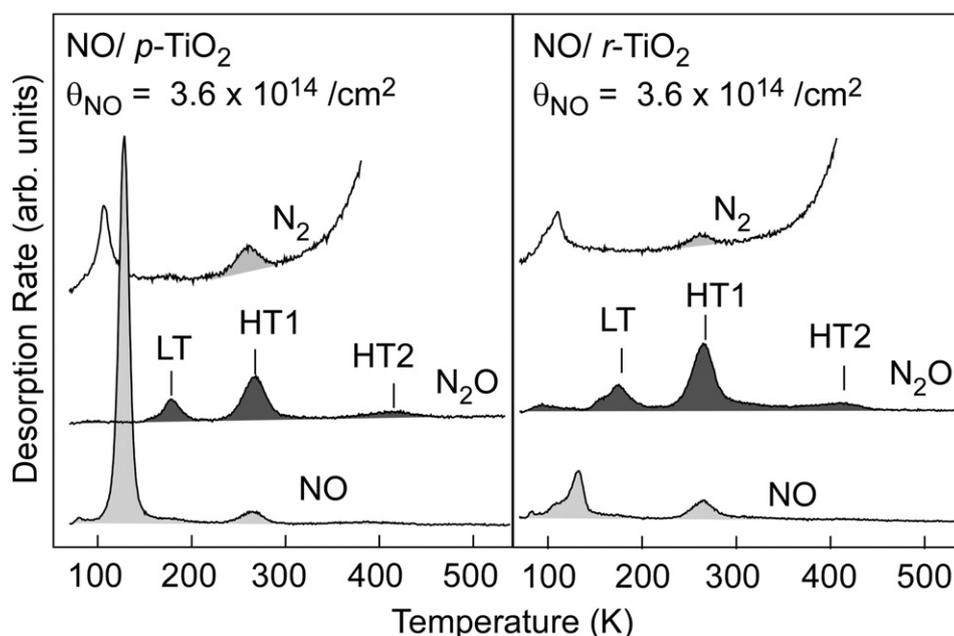


Fig. 1. NO, N_2O , and N_2 TPD spectra following NO adsorption ($\theta_{\text{NO}} = 3.6 \times 10^{14} \text{ NO}/\text{cm}^2$) on (a) *p-TiO₂* (concentration of V_{O} 's is <0.01 ML) and (b) *r-TiO₂* (concentration of V_{O} 's is 0.05 ML) at 50 K. The TPD spectra were acquired using a constant ramp rate of 1 K/s.

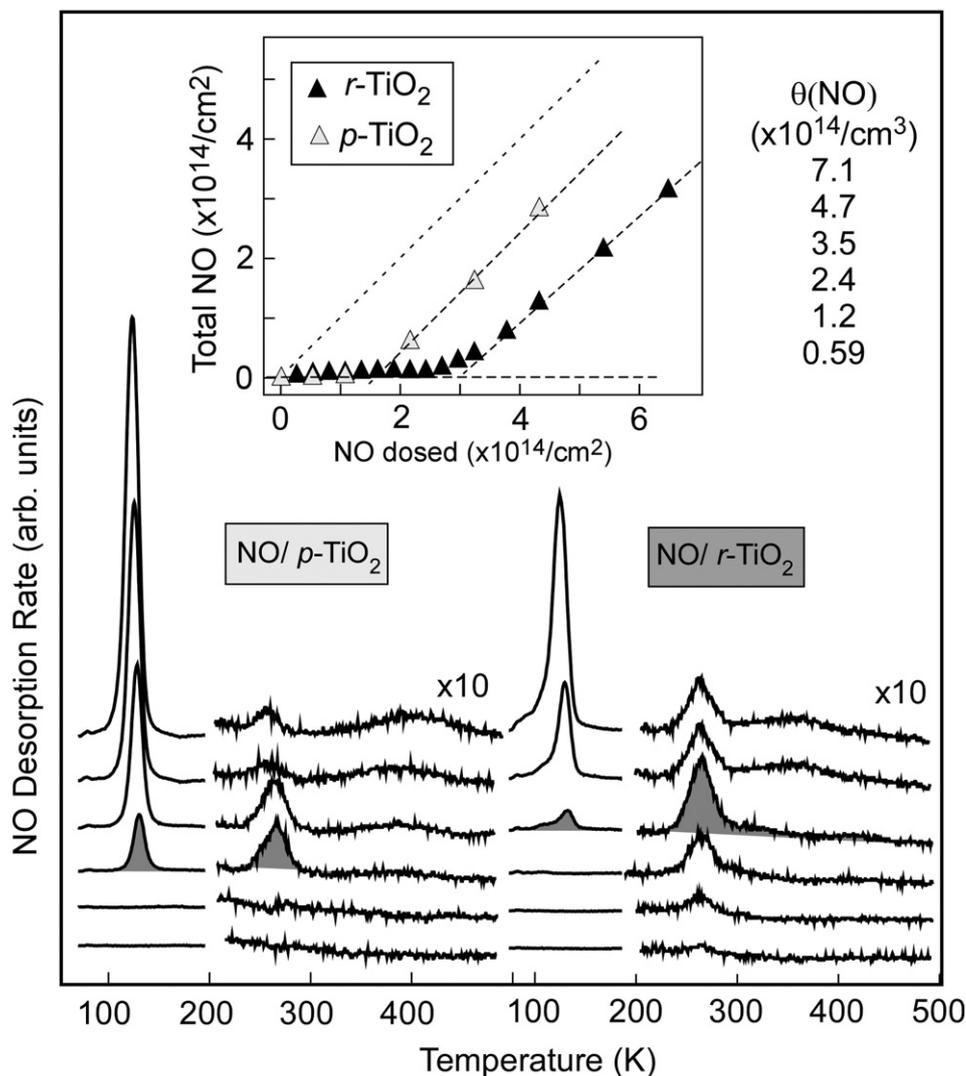


Fig. 2. NO TPD spectra from NO dosed on *p*- and *r*-TiO₂ as a function of NO dose. The inset shows the integrated amount of desorbing NO vs. NO dose. The number of Ti⁴⁺ sites on the surface is $5.2 \times 10^{14}/\text{cm}^2$ (≈ 1 ML).

doses ($\sim 1 \times 10^{14}$ NO/cm²), nearly all NO reacts to form products such as N₂O and NO₂. NO desorption is observed only above a certain threshold dose, which is 2.5×10^{14} NO/cm² for *r*-TiO₂ and 1×10^{14} NO/cm² for *p*-TiO₂. This result clearly shows that more NO reacts on *r*-TiO₂ than on *p*-TiO₂. Since the key difference between these two surfaces is the high concentration of V_O's ($\sim 5\%$) on *r*-TiO₂, the V_O's are attributed to the higher reactivity of *r*-TiO₂ than that of *p*-TiO₂ as has been observed from the role of V_O's in the enhanced LT N₂O formation yield [14].

Fig. 3 shows N₂O TPD spectra for different NO doses on *p*- and *r*-TiO₂. On both surfaces, the HT1 N₂O peak initially increases, maximizes at NO dose of $\sim 3.5 \times 10^{14}$ NO/cm² and subsequently decreases at higher NO doses. The HT2 N₂O peak is relatively small but shows a similar NO dose-dependent trend as the HT1 N₂O desorption peak. By contrast, the LT N₂O peak increases proportionally with the NO dose. A comparison of the N₂O spectra from *r*- and *p*-TiO₂ reveals that the trends are very similar except that the overall N₂O desorption yield is higher on *r*-TiO₂ at higher NO doses.

At low NO doses, the intensity of N₂O desorption peaks from *p*-TiO₂ is slightly higher than that from *r*-TiO₂. Since more N₂O desorption occurs during the NO dose on *r*-TiO₂, it is likely that more oxygen adatoms are left on the *r*-TiO₂ at the low NO dose regime. It may facilitate the formation of further oxidized forms of NO such as NO₂ and NO₃ better on *r*-TiO₂ than on *p*-TiO₂. This may act as a factor of suppressing the yield of the

reductive channel (N₂O desorption) on *r*-TiO₂ than on *p*-TiO₂ at the low NO dose regime.

The integrated N₂O amounts observed in three observed N₂O TPD peaks (LT, HT1, and HT2) as well as the total N₂O from both *r*-TiO₂ and *p*-TiO₂ are plotted against the NO dose in Fig. 4. Several interesting features can be observed in the NO coverage-dependent trends of N₂O desorption yield. First, the total N₂O yield increases up to the NO dose of 2.5×10^{14} and 4×10^{14} NO/cm² on *p*- and *r*-TiO₂, respectively, then saturates at higher doses. The total N₂O yield from *r*-TiO₂ is higher than that from *p*-TiO₂ by $\sim 3.5 \times 10^{13}/\text{cm}^2$. This can be attributed to the presence of V_O's on *r*-TiO₂. The V_O's also lead to the N₂O desorption below 100 K from NO dosed on *r*-TiO₂(110) [14]. Some of N₂O formed at the dose temperature is physisorbed and desorbs below 200 K during the TPD ramp. N₂O may be also formed during the ramp as the molecularly bound NO species diffuse on the surface and react with each other forming N₂O + O_a at low temperatures (up to 120 K). These possible channels contribute to LT N₂O desorption below 200 K.

Second, the HT1 N₂O yield does not saturate, but decreases at higher NO doses. The maximum yield of HT1 N₂O is reached at the NO dose of 2.5×10^{14} and 3.5×10^{14} NO/cm² on *p*- and *r*-TiO₂, respectively, which decreases as the NO dose increases further. The loss in HT1 N₂O yield is largely compensated by an increase in the LT N₂O yield; this results in a saturation in the total N₂O yield for both *r*- and *p*-TiO₂. As the NO dose

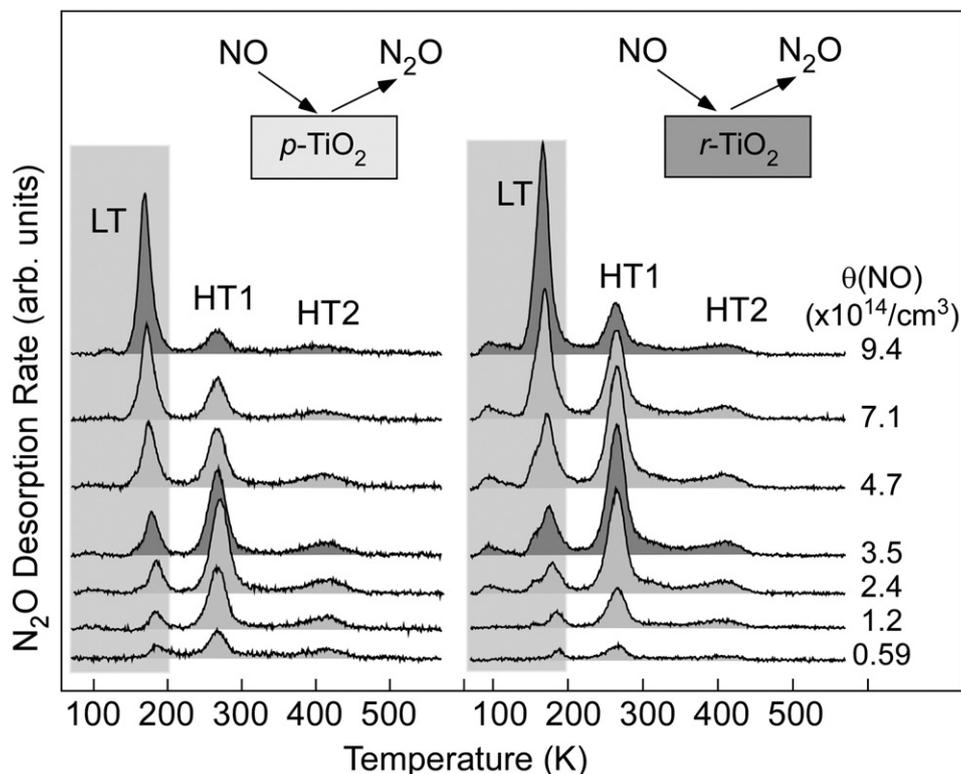


Fig. 3. TPD spectra of N_2O desorption from NO dosed on two different TiO_2 surfaces (p - TiO_2 and r - TiO_2) with increasing NO dose.

increases to a saturation of monolayer, the increased NO–NO interaction may facilitate the formation of N_2O at lower temperatures (<200 K); it may limit the formation of the surface NO-derived species responsible for the HT N_2O such as stable forms of NO dimers. The absolute yield for the HT2 N_2O is low, but the NO dose-dependent trend follows a similar trend as HT1.

Third, there is a deficiency between the NO dose and the sum of NO and N_2O desorption yields. For example, for the NO dose of 3.5×10^{14} NO/cm² on r - TiO_2 , the total N_2O yield is $\sim 8 \times 10^{13}$ N_2O /cm², and the amount of unreacted NO desorption is about 5×10^{13} NO/cm². After adding the N_2O desorption during the NO dose ($\sim 1 \times 10^{13}$ N_2O /cm²), the total N_2O yield equals to $\sim 9 \times 10^{13}$ N_2O /cm² accounting for the NO

dose of 1.8×10^{14} NO/cm². The desorbing amounts of NO and N_2O account for 2.3×10^{14} NO/cm². Thus, a significant fraction of NO ($\sim 1.2 \times 10^{14}$ NO/cm²) remains unaccounted. This discrepancy is larger than that expected from a possible calibration error (~ 10 – 20%), which leads us to conclude that there are N species that are not desorbed from the surface during TPD up to about 650 K. It is likely that oxidized species such as NO_2 and NO_3 are left on the surface. We cannot detect further desorption of any N-related species above 500 K up to 850 K. In addition, XPS measurements carried out after the NO TPD up to 200–500 K sometimes show noisy signals at 400–406 eV only at the first scan, which quickly disappear at the subsequent scans, resulting in no meaning features of N 1s spectra. We believe that this is because

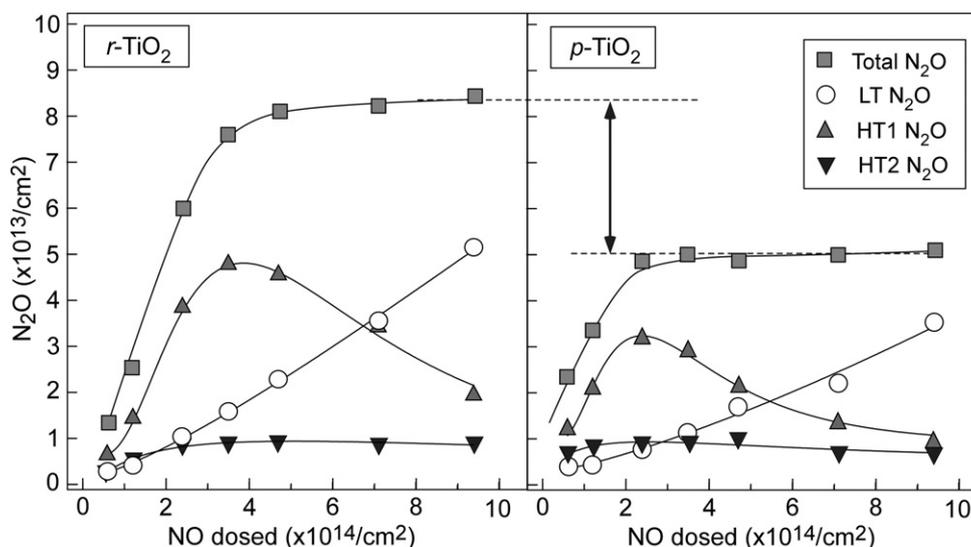


Fig. 4. The integrated amounts of N_2O for the three different channels, LT, HT1, and HT2 as well as that of total N_2O obtained from TPD peaks in Fig. 3 as a function of NO dose on p - and r - TiO_2 .

such NO_2 and NO_3 species are very unstable under x-ray irradiation in a UHV condition. Thus, we speculate that they are oxidized forms of NO such as NO_2 and NO_3 , which can be produced by reactions of NO with oxygen adatoms.

However, a small measurable amount of stable N species is found from XPS after several cycles of NO TPD (> 10 cycles). This fact also supports the idea that there are surface N species left from NO reactions on TiO_2 , in oxidized forms such as NO_2 and NO_3 ; several cycles of TPD may induce the formation of stable NO_3 aggregates instead of the isolated NO_3 .

A strong correlation between V_O 's on $r\text{-TiO}_2$ and the NO reactivity is further corroborated from Fig. 5. It shows H_2O TPD obtained after NO TPD up to 400 K at various NO doses. After the NO TPD, H_2O is dosed to probe the V_O sites that remain following the NO adsorption and reactions. The same method has been used to determine the concentration of V_O 's on bare $r\text{-TiO}_2$ surfaces as described in the experimental section [19,21,25]. The H_2O TPD spectra in Fig. 5 show that the recombinative H_2O desorption peak at 500 K ($2\text{OH}_b \rightarrow \text{H}_2\text{O}(\text{g}) + \text{O}_b + V_O$) decreases significantly already at very low NO doses ($< 5 \times 10^{13} \text{ NO}/\text{cm}^2$). The dependence of the integral of the recombinative H_2O TPD peak on the NO dose is shown in the upper inset of Fig. 5. The observed dependence

shows that the V_O concentration decreases quite in proportion to the NO dose and that it is reduced to one third of the initial value ($2.6 \times 10^{13} V_O/\text{cm}^2$) at $\sim 5 \times 10^{13} \text{ NO}/\text{cm}^2$. We speculate that this is the result of V_O 's being preferentially filled with oxygen atoms left behind from the N_2O formation from NO [14].

Considering that the formation of N_2O from NO leaves O_a on $\text{TiO}_2(110)$, the effect of predosed oxygen on the reactivity of NO is investigated in Fig. 6. The figure shows the TPD spectra of NO and N_2O from NO dosed on O_2 -predosed $r\text{-TiO}_2$ at fixed NO dose ($\theta_{\text{NO}} = 3.5 \times 10^{14} \text{ NO}/\text{cm}^2$), while the O_2 dose is increased up to $3.5 \times 10^{14}/\text{cm}^2$. NO TPD (left) shows that the LT NO desorption increases with increasing O_2 , suggesting that the reactivity of NO over TiO_2 decreases due to the effect of predosed O_2 . As a result, unreacted NO contributes to the increase of NO desorption yield with increasing O_2 dose as quantified in the left inset of Fig. 6. The TPD spectra of N_2O (right) show that the total N_2O desorption yield decreases with increasing O_2 doses.

The N_2O desorption yield from different channels is shown in the upper right inset of Fig. 6. Note that the decrease of HT1 N_2O yield is more pronounced than that of LT N_2O . As the predosed O_2 increases, the HT1 N_2O yield vanishes at an O_2 dose of $\sim 2 \times 10^{14} \text{ O}_2/\text{cm}^2$, while

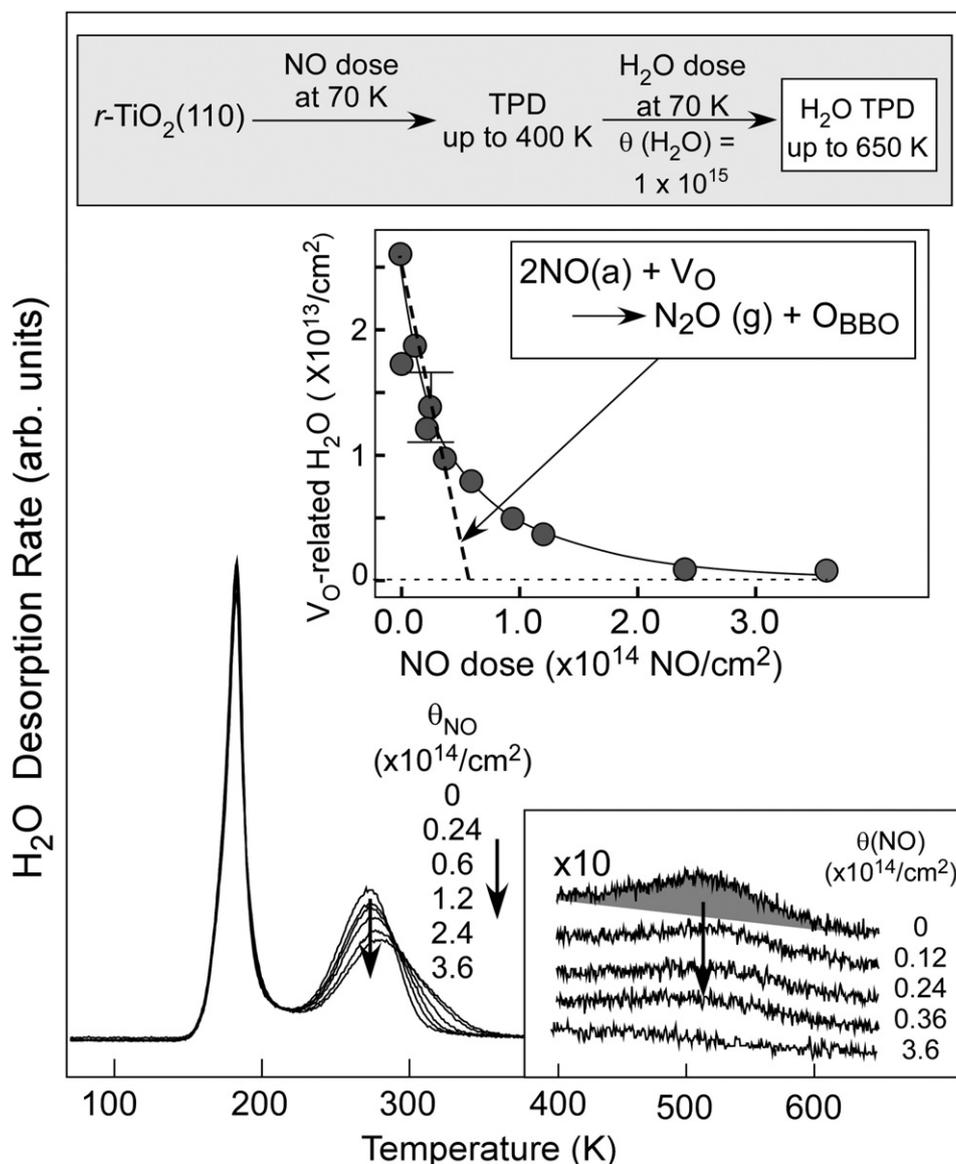


Fig. 5. H_2O TPD (dose = $1 \times 10^{15} \text{ H}_2\text{O}/\text{cm}^2$) from $r\text{-TiO}_2$ after dosing different amounts of NO at 70 K and TPD to 400 K. The recombinative H_2O desorption at 500 K (bottom inset) from available V_O sites shows that V_O 's are readily depleted as a result of NO adsorption and reaction.

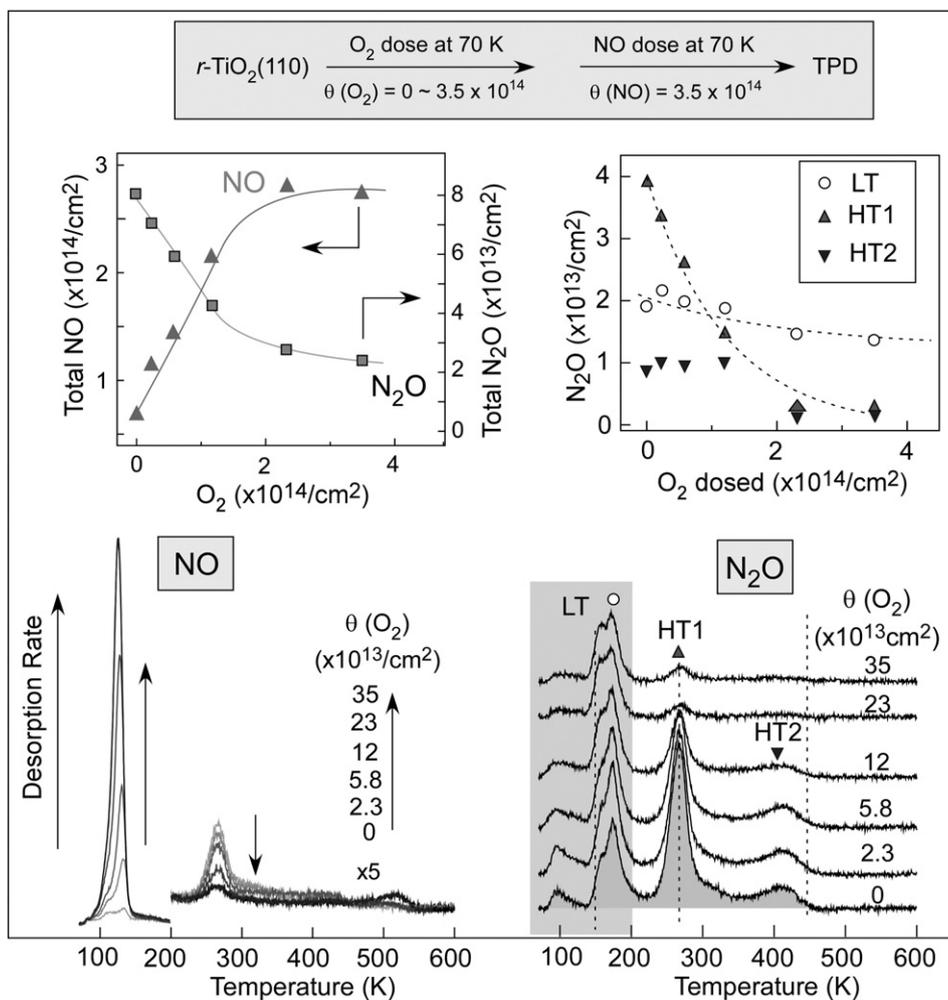


Fig. 6. TPD spectra showing NO (left) and N₂O (right) desorption from NO dosed on O₂-predosed *r*-TiO₂. The insets show the total NO (top left) and N₂O (top right) yields for various N₂O desorption channels plotted as a function of the O₂ dose.

the LT N₂O yield persists. Thus, the formation of surface NO-derived species responsible for the HT N₂O is more likely to be suppressed by the presence of predosed O₂ probably via the depletion of surface charge associated with oxygen vacancies. The predosed O₂ may fill the oxygen vacancies which can otherwise act as a binding site for NO dimers, e.g., (NO)₂⁻. The NO dimer ((NO)₂⁻) can be a likely candidate for HT1 N₂O peak since the decomposition of the dimer into N₂O and O_a at ~270 K can readily induce desorption of N₂O (reaction-limited desorption).

The LT N₂O yield is also suppressed slightly but still shows a significant desorption yield of ~1.5 × 10¹³ N₂O/cm² even at 3.5 × 10¹⁴ O₂/cm². Despite the persistent nature of the LT N₂O yield, we have also seen that during the NO dose on *r*-TiO₂, the LT N₂O desorption at the dose temperature (~50 K) is also strongly influenced by the depletion of surface charges by predosed O₂ [14]. In Fig. 6, NO is subsequently dosed following the O₂ dose at the low temperature and the TiO₂ is not fully oxidized under the condition. It is attributed to the origin of the persistent LT N₂O yield.

The effect of oxygen on the N₂O desorption channels is further studied by comparing N₂O TPD spectra taken from NO dosed on two different TiO₂ surfaces of *o*-TiO₂ and *r*-TiO₂, respectively. On *o*-TiO₂ (Fig. 7(a)), LT N₂O desorption is observed only above 4 × 10¹⁴ NO/cm²; no HT N₂O desorption is observed throughout the whole NO doses up to 1 × 10¹⁵ NO/cm². This is consistent with earlier observations of Sorescu *et al.* on N₂O desorption from oxidized TiO₂(110) [12]. We can speculate that the formation of possible surface precursors (e.g., NO dimers) for the

HT N₂O desorption channels is inhibited as a result of the depletion of V_O's (as well as surface charges associated with them).

Fig. 8 shows the behavior of the HT N₂O desorption channels when the surface is hydroxylated (*h*-TiO₂). Fig. 8(a) compares N₂O TPD spectra taken from three different TiO₂ surfaces: *r*-TiO₂, *h*-TiO₂, and H₂O predosed *h*-TiO₂. Note that the HT1 N₂O desorption peak is significantly reduced on *h*-TiO₂ compared to *r*-TiO₂, while the LT and HT2 N₂O desorption peaks are greatly enhanced. The HT1 N₂O is nearly depleted when a small amount of H₂O (~2 × 10¹³ H₂O/cm²) is predosed on the *h*-TiO₂. The quantitative evaluation on the three N₂O yields is displayed in Fig. 8(b). The sum of N₂O on *h*-TiO₂ is slightly lower than that on *r*-TiO₂ by ~0.5 × 10¹³ N₂O/cm² due to the formation of NH₃ from the reaction between HO_b's and NO [28].

The data presented above imply that the presence of hydroxyls (and water) can deplete the surface species (probably (NO)₂⁻) that lead to the HT1 N₂O desorption channel. Despite the quenching of the HT1 N₂O channel, the total N₂O yield does not vary much over the three TiO₂ surfaces. Recent STM studies performed at RT [29] show that the adsorbed NO is stabilized next to the hydroxyl species. We speculate that the low-temperature NO adsorption can possibly also yield more stable (NO)₂⁻ dimers on *h*-TiO₂ than on *r*-TiO₂. Such species can be a source of the HT2 N₂O desorption that is observed on *h*-TiO₂.

Oxidized NO species such as NO₂ may be further oxidized by H₂O to make nitrate (NO₃) as has been reported earlier on oxide surfaces [30], including TiO₂ [31]. HO_b's on *h*-TiO₂ may react with O_a's to form OH_i's on the Ti⁴⁺ rows on the TiO₂(110) surface [32], subsequently forming H₂O

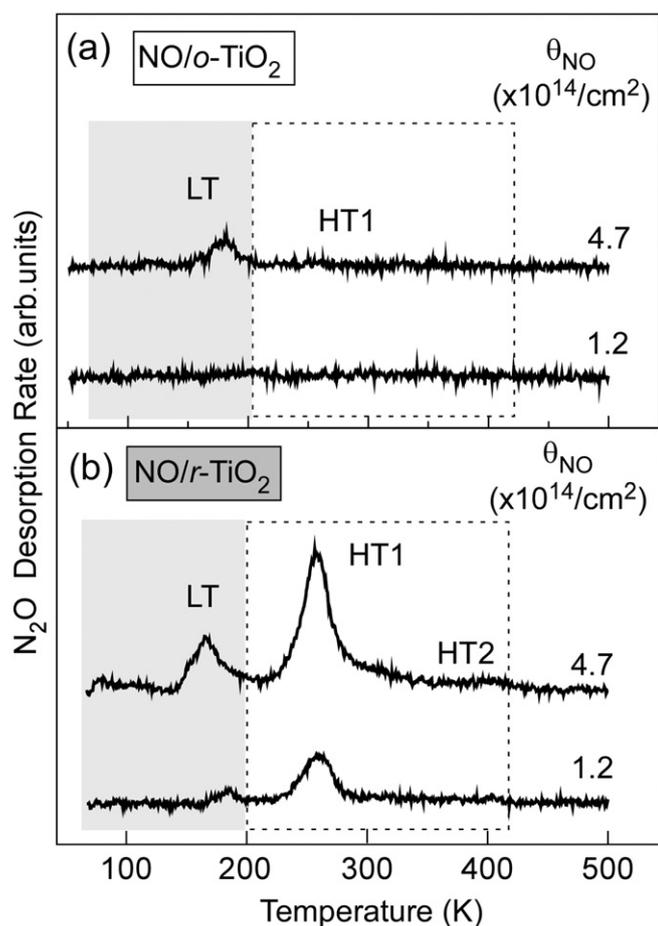


Fig. 7. Comparison of TPD spectra of N_2O desorbing from NO dosed on (a) o - TiO_2 and (b) r - TiO_2 , respectively.

which desorbs at 300–400 K. Coadsorbed H_2O also interacts with O_3 to form OH_t 's [33]. Such OH_t species may react with NO_2 to form HNO_3 , which can dissociate into H^+ and NO_3^- on TiO_2 . However, this process is not likely to change the total N_2O yield as long as NO_2 and NO_3 do not contribute to the N_2O desorption channels.

The presence of hydroxyls also enhances the formation of LT N_2O (Fig. 8). The detailed mechanism for the enhanced LT N_2O desorption on h - TiO_2 is unclear, but we speculate that the presence of hydroxyls (and water) may also stabilize the adsorbed NO toward LT N_2O formation channel, probably via NO dimers.

We postulate that possible candidates for surface species responsible for the HT N_2O desorption channels can be NO dimers (e.g., $(NO)_2^-$) and hydroxyl-stabilized NO dimers for HT1 and HT2 N_2O , respectively. NO reduction on metal surfaces such as Ag [34,35], Au [36], Cu [37], and Pd [38] is proposed to involve $(NO)_2$ dimers as intermediates. In addition, such coupled NO species in the form of hyponitrite $(N_2O_2)^{2-}$ are also proposed as the intermediates of NO reduction cycles in biological systems employing NO reductase (NOR) [39] and flavodiiron NO reductase (FDP) [40].

NO dimers of various forms (e.g., cis and trans) have been proposed to have binding energies of 10–15 kcal/mol theoretically [12,41], which vary depending on the bonding configuration; they are suggested to decompose into $N_2O(a)$ and O_a below 200 K according to a recent FTIR study [41]. However, charged $(NO)_2^{2-}$ species may survive above 200 K and possibly contribute to HT1 N_2O desorption as previously observed for NO reactions on MnO_x/CeO_2 at 295 K [42]. In addition, bonding configuration of the NO dimers such as cis or trans can determine the energy barrier toward N_2O formation [43], which may give rise to N_2O desorption at different temperatures. Then, the observed variation

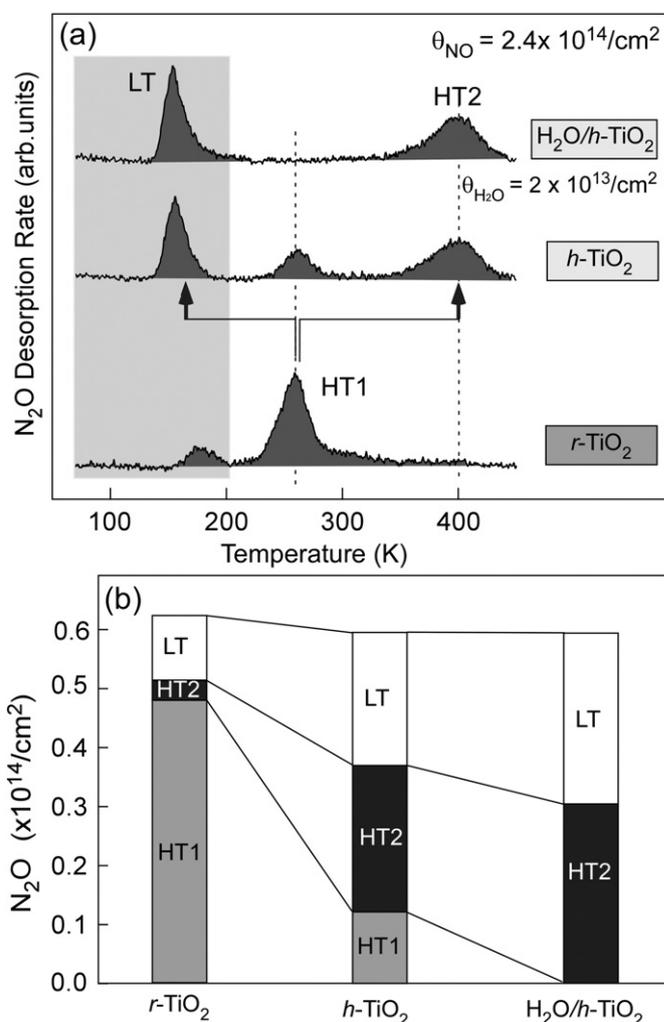


Fig. 8. (a) Comparison of TPD spectra of N_2O desorbing from NO (NO dose = 2.4×10^{14} NO/cm^2) dosed on r - TiO_2 , h - TiO_2 , and H_2O/h - TiO_2 , respectively. It shows an intensity variation of each N_2O desorption channel on three different TiO_2 surfaces. (b) The N_2O desorption yields of LT, HT1, and HT2 channels compared for three different substrates of r - TiO_2 , h - TiO_2 , and H_2O pre-dosed h - TiO_2 . NO dose is fixed to 2.4×10^{14} NO/cm^2 .

in N_2O desorption channels above the threshold NO dose in Fig. 4 may be the result of varying ratio between different bonding configurations (e.g., cis and trans) with increasing NO doses. At low NO coverages the formation of trans-hyponitrites are favored and N_2O desorption is observed in the HT1 state primarily. As the surface becomes more crowded at higher NO exposures, the formation of cis-hyponitrites is prevalent. Since the decomposition of cis-hyponitrites is energetically less demanding than that of the trans conformer, N_2O desorption is observed in the LT state as the NO exposure increases.

NO_2 has been suggested to be formed from NO dosed on $TiO_2(110)$ both experimentally and theoretically [15,16]. Theoretical studies [15, 44] on NO_2/TiO_2 indicate that NO_2 is more strongly bound to TiO_2 than NO when NO_2 is bound to the Ti sites with its two oxygen atoms (η^2 -bonding configuration). NO_2 may be further oxidized to NO_3 species, which are likely to survive above 400 K [31,44], too. The formation of oxidized species such as NO_2 and NO_3 on the surface is suggested to be the origin of the discrepancy in the total amount of NO dosed and that desorbed in Fig. 4.

4. Conclusions

A systematic temperature-programmed desorption (TPD) study of NO reactions with rutile $TiO_2(110)$ surface has been performed. Low-

temperature (<200 K, LT N₂O), desorption-limited, and high-temperature (>200 K, HT N₂O) reaction-limited N₂O formation channels are observed in the TPD spectra. The insight obtained from these results is summarized below.

- (i) The LT N₂O desorption channel increases approximately linearly on reduced TiO₂(110) (*r*-TiO₂) with increasing NO coverages. The branching into this channel is strongly reduced in the absence of surface charge associated with bridging oxygen vacancies (V_O's) as evident from the comparison of NO reactivity on *r*-TiO₂ and *o*-TiO₂ (TiO₂(110) surface oxidized by O₂).
- (ii) The HT N₂O yield exhibits a maximum at intermediate NO doses but decreases as the NO dose is increased further. The maximum yield is obtained at a NO dose of 3.5×10^{14} and 2.5×10^{14} NO/cm² for *r*-TiO₂ and *p*-TiO₂ (TiO₂(110) with negligible V_O coverage). The observed HT N₂O decrease is correlated with increased LT N₂O formation; this results in a saturation in the overall N₂O yield above the intermediate NO dose.
- (iii) The higher HT N₂O yield on *r*-TiO₂ as compared to *p*-TiO₂ indicates the importance of V_O's (and surface charges associated with them) in the formation of surface species responsible for the HT channel. The importance of surface charge is further supported by suppression of the HT N₂O desorption channel in the presence of the predosed oxygen.
- (iv) There are also reaction-limited N₂ and NO desorption peaks at the same temperature as the HT1 N₂O desorption, which may be attributed to the competition between the three competing reaction channels originating from the same surface species.
- (v) The HT2 N₂O desorption channel (along with the LT N₂O channel) is enhanced in the presence of hydroxyls (*h*-TiO₂), while the HT1 N₂O desorption channel is reduced. The suppression of the HT1 N₂O channel and the appearance of a new HT2 N₂O channel on *h*-TiO₂ is likely the result of stabilization of NO (dimers) in the presence of hydroxyls.
- (vi) The discrepancy between the amount of NO dosed and that desorbed exists; it is likely the result of formation of oxidized species such as NO₂ and NO₃.

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